

8.0 AMPS. Glass Passivated Fast Recovery Rectifiers

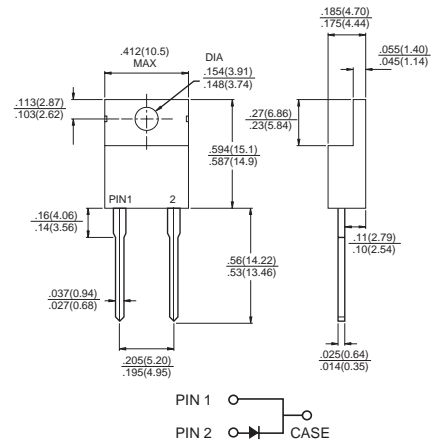
FEATURES

- Glass passivated chip junction.
- High efficiency, Low VF
- High current capability
- High reliability
- High surge current capability
- Low power loss

MECHANICAL DATA

- Cases: TO-220AC Molded plastic
- Epoxy: UL 94V-0 rate flame retardant
- Terminals: Pure tin plated, Lead free. Leads solderable per MIL-STD-202, Method 208 guaranteed
- Polarity: As marked
- High temperature soldering guaranteed:
260 °C /10 seconds .16", (4.06mm) from case.
- Mounting position: Any
- Weight: 2.24 grams

TO-220AC



Dimensions in inches and (millimeters)



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25 °C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load.

For capacitive load, derate current by 20%

Type Number	Symbol	FRA 801G	FRA 802G	FRA 803G	FRA 804G	FRA 805G	FRA 806G	FRA 807G	Units
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current @ $T_c = 55^\circ C$	$I_{(AV)}$	8.0							A
Peak Forward Surge Current, 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I_{FSM}	150							A
Maximum Instantaneous Forward Voltage @ 8.0A	V_F	1.3							V
Maximum DC Reverse Current @ $T_c=25^\circ C$ at Rated DC Blocking Voltage @ $T_c=125^\circ C$	I_R	5.0 100							uA uA
Maximum Reverse Recovery Time (Note 2)	T_{rr}	150			250	500			nS
Typical Junction Capacitance (Note 1) $T_{J}=25^\circ C$	C_j	50							pF
Typical Thermal Resistance (Note 3)	$R_{\theta JA}$	3.0							°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-65 to +150							°C

- Notes:
1. Measured at 1 MHz and Applied Reverse Voltage of 4.0 Volts D.C.
 2. Reverse Recovery Test Conditions: $I_F=0.5A$, $I_R=1.0A$, $I_{RR}=0.25A$
 3. Thermal Resistance from Junction to Case, with Heatsink size 2" x 3" x 0.25" Al-Plate.

RATINGS AND CHARACTERISTIC CURVES (FRA801G THRU FRA807G)

FIG.1- MAXIMUM FORWARD CURRENT DERATING CURVE

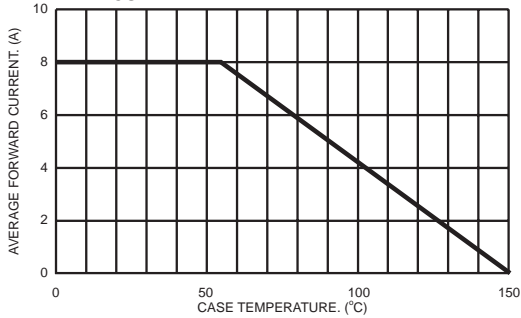


FIG.2- TYPICAL REVERSE CHARACTERISTICS

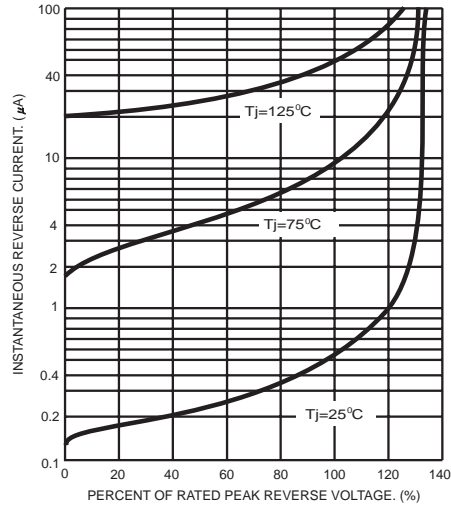


FIG.3- MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

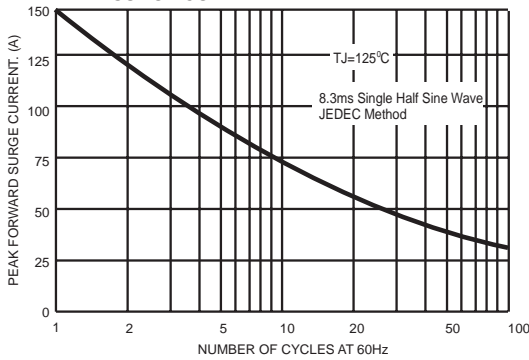


FIG.5- TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

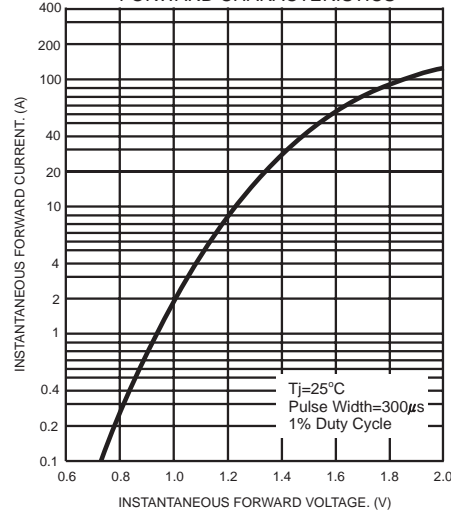


FIG.4- TYPICAL JUNCTION CAPACITANCE

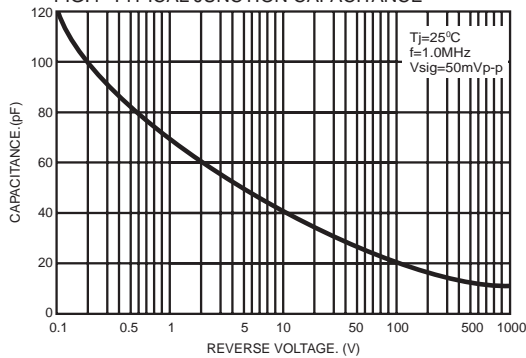
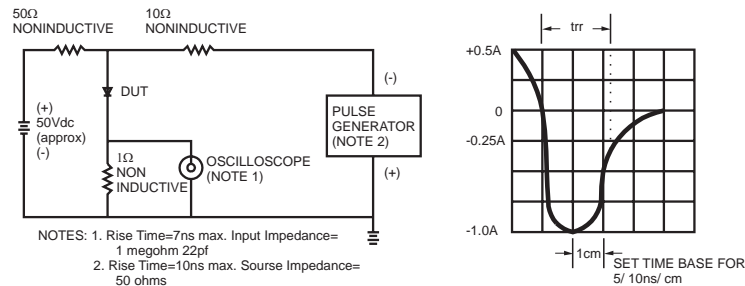


FIG.6- REVERSE RECOVERY TIME CHARACTERISTIC AND TEST CIRCUIT DIAGRAM



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